



Nine-Output, 200-MHz Zero Delay Buffer

Features

- 50-MHz to 200-MHz operating range
- 650-ps max. Total Timing Budget™ (TTB™) window
- Nine low-skew outputs, grouped as 4 + 4 + 1
 - Output-output Skew < 200 ps
 - Device-device Skew < 500 ps
- Input-output skew < 250 ps
- Cycle-cycle jitter < 100 ps
- Three-stateable outputs
- < 50-μA shutdown current
- Spread Aware™
- Phase-locked loop (PLL) bypass mode (see Table 1)
- 16-pin TSSOP
- 3.3V operation
- Commercial/Industrial temperature

Description

The CY2309A is a high-performance 200-MHz zero delay buffer designed for high-speed clock distribution. The integrated PLL is designed for low jitter and optimized for noise

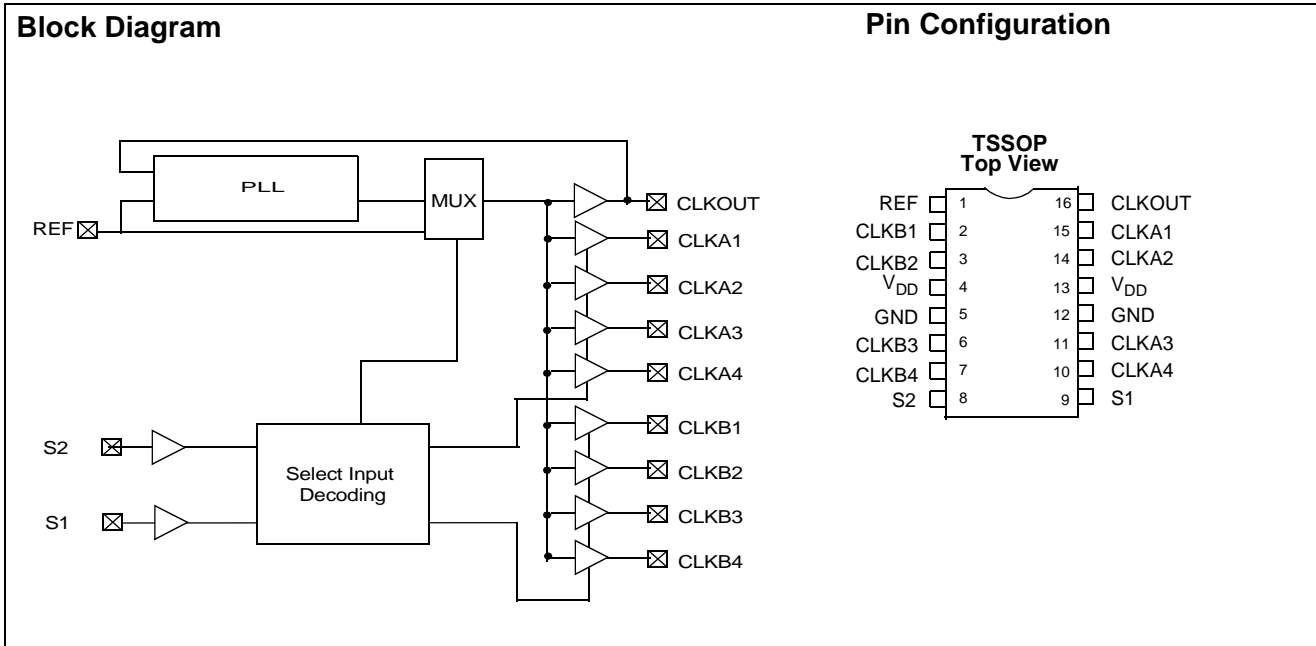
rejection. These parameters are critical for reference clock distribution in systems using high-performance ASICs and microprocessors. The CY2309A PLL feedback is internal and is connected to CLKOUT.

The device features a guaranteed maximum TTB window specifying all occurrences of output clocks with respect to the input reference clock across variations in output frequency, supply voltage, operating temperature, input edge rate, and process.

The CY2309A has two banks of four outputs each, which can be controlled by the select inputs as shown in Table 1. If all the output clocks are not required, Bank B can be three-stated. The select inputs also allow the input clock to be directly applied to the outputs for chip and system testing purposes (PLL bypass mode).

The CY2309A PLL enters a power-down state when there are no rising edges on the REF input. In this mode, all outputs are three-stated and the PLL is turned off, resulting in less than 50 μA of current draw. The PLL shuts down in two additional cases, as shown in Table 1.

The CY2309A is available in standard (–1) or high-drive (–1H) output versions. The high-drive features faster rise and fall times.



Pin Description

Pin	Name	Description
1	REF	Input reference frequency, 5V-tolerant input
2	CLKB1 ^[1]	Clock output, Bank B
3	CLKB2 ^[1]	Clock output, Bank B
4	V _{DD}	3.3V Supply
5	GND	Ground
6	CLKB3 ^[1]	Clock output, Bank B
7	CLKB4 ^[1]	Clock output, Bank B
8	S2 ^[2]	Select input, 5V-tolerant input
9	S1 ^[2]	Select input, 5V-tolerant input
10	CLKA4 ^[1]	Clock output, Bank A
11	CLKA3 ^[1]	Clock output, BankA
12	GND	Ground
13	V _{DD}	3.3V supply
14	CLKA2 ^[1]	Clock output, Bank A
15	CLKA1 ^[1]	Clock output, Bank A
16	CLKOUT ^[1]	Clock output, internal feedback on this pin

Table 1. Select Input Decoding

S2	S1	CLOCK A1–A4	CLOCK B1–B4	CLKOUT ^[3]	Output Source	PLL Shutdown
0	0	Three-state	Three-state	Driven	PLL	N
0	1	Driven	Three-state	Driven	PLL	N
1	0	Driven	Driven	Driven	Reference	Y
1	1	Driven	Driven	Driven	PLL	N

Zero Delay and Skew Control

Since the CLKOUT is the internal feedback to the PLL, its relative loading can adjust the input-output delay. See *Figure 1* For applications requiring zero input-output delay, all outputs, including CLKOUT, must be equally loaded. Even if CLKOUT is not used, it must have a capacitive load, equal to that on other outputs, for obtaining zero input-output delay. If input-output delay adjustments are required, use the above graph to calculate loading differences between the CLKOUT and other outputs.

For zero output-output skew, be sure to load all outputs equally. For further information on using CY2309A, refer to the application note “CY2309 as PCI and SDRAM Buffers.”

Notes:

1. Weak pull-down.
2. Weak pull-up.
3. This output is driven and has an internal feedback for the PLL. The load on this output can be adjusted to change the skew between the reference and output.

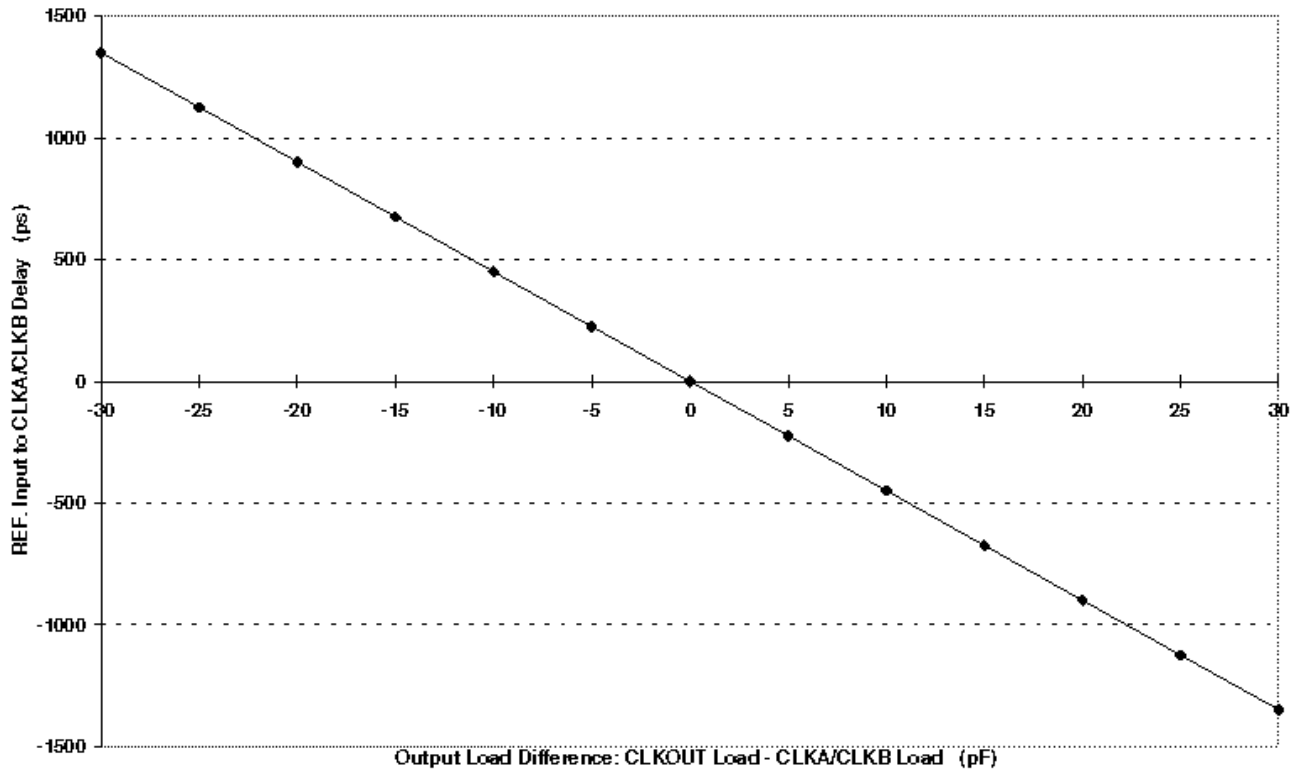


Figure 1. REF. Input to CLKA/CLKB Delay vs. Difference in Loading between CLKOUT and CLKA/CLKB

Maximum Ratings

Supply Voltage to Ground Potential -0.5V to +7.0V
 DC Input Voltage (Except REF, S2, S1) -0.5V to $V_{DD} + 0.5V$
 DC Input Voltage (REF, S1, S2) -0.5V to 7.0V
 Storage Temperature -65°C to +150°C
 Junction Temperature 125°C
 Junction-to-Ambient Thermal Resistance
 16-pin TSSOP 115°C/W

Static Discharge Voltage
 (per MIL-STD-883, Method 3015) > 2000V

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of any voltage higher than the maximum rated voltages to this circuit. For proper operation, V_{in} and V_{out} should be constrained to the range:

$$V_{SS} < (V_{in} \text{ or } V_{out}) < V_{DD}$$

Unused inputs must always be tied to an appropriate logic voltage level (either V_{SS} or V_{DD}).

Table 2. Operating Conditions for CY2309AZC-XX Commercial Temperature Devices

Parameter	Description	Min.	Max.	Unit
V_{DD}	Supply Voltage	3.135	3.465	V
T_A	Operating Temperature (Ambient Temperature)	0	70	°C
C_{IN}	Input Capacitance		7	pF
t_{PU}	Power-up time for all VDDs to reach minimum specified voltage (power ramps must be monotonic)	0.05	500	ms

Table 3. Electrical Characteristics for CY2309AZC-XX Commercial Temperature Devices

Parameter	Description	Test Conditions	Min.	Max.	Unit
V_{IL}	Input LOW Voltage	CMOS Levels, 30% of V_{DD}		0.25	V_{DD}
V_{IH}	Input HIGH Voltage	CMOS Levels, 70% of V_{DD}	0.7		V_{DD}
I_{IL}	Input LOW Current	$V_{IN} = 0V$		50	μA
I_{IH}	Input HIGH Current	$V_{IN} = V_{DD}$		10	μA
I_{OL}	Output LOW Current ^[4] , (-1)	$V_{OL} = 0.5V$	12		mA
	(-1H)		18		
I_{OH}	Output HIGH Current ^[4] , (-1)	$V_{OH} = V_{DD} - 0.5V$		-12	mA
	(-1H)			-18	
I_{DD5}	Power-down Supply Current	REF = 0V, S1 = V_{DD} , S2 = V_{DD}		50	μA
I_{DD}	Supply Current	Unloaded outputs @ 200 MHz		115	mA
		Loaded outputs @ 200 MHz, $C_L = 10$ pF		145	

Table 4. Switching Characteristics for CY2309AZC-XX Commercial Temperature Devices^[5]

Parameter	Description	Test Conditions	Min.	Typ.	Max.	Unit
	Reference Frequency		50		200	MHz
	Reference Edge Rate	30% to 70% of V_{DD}	0.5		4	V/ns
	Reference Duty Cycle		25		75	%
t_1	Output Frequency	$C_L = 10$ pF	50		200	MHz
		$C_L = 15$ pF	50		140	
	Duty Cycle ^[4] = t_2 / t_1	Measured at $V_{DD}/2$	45	50	55	%
t_3	Rising Edge Rate ^[4] , (-1)	20% to 80% of V_{DD} , $C_L = 15$ pF	0.8		4	V/ns
	Rising Edge Rate ^[4] , (-1H)	20% to 80% of V_{DD} , $C_L = 15$ pF	1		4	
t_4	Falling Edge Rate ^[4] , (-1)	80% to 20% of V_{DD} , $C_L = 15$ pF	0.8		4	V/ns
	Falling Edge Rate ^[4] , (-1H)	80% to 20% of V_{DD} , $C_L = 15$ pF	1		4	

Notes:

- Parameter is guaranteed by design and characterization. Not 100% tested in production.
- All parameters specified with loaded outputs.

Table 4. Switching Characteristics for CY2309AZC-XX Commercial Temperature Devices^[5] (continued)

Parameter	Description	Test Conditions	Min.	Typ.	Max.	Unit
TTB	Total Timing Budget window ^[6]	Outputs @ 200 MHz, Tracking Skew Not Included			650	ps
t ₅	Output to Output Skew ^[4]	All Outputs Equally Loaded			200	ps
t ₆	Input to Output Skew (Static Phase Error) ^[4]	Measured at V _{DD} /2, REF to CLKOUT			250	ps
t ₇	Device to Device Skew ^[4]	Measured at V _{DD} /2			500	ps
t _J	Cycle to Cycle Jitter ^[4]	Loaded Outputs			200	ps
					35	ps _{RMS}
t _{LOCK}	PLL Lock Time ^[4]	Stable Power Supply, Valid Clock at REF			1.0	ms

Table 5. Operating Conditions for CY2309AZI-XX Industrial Temperature Devices

Parameter	Description	Min.	Max.	Unit
V _{DD}	Supply Voltage	3.135	3.465	V
T _A	Operating Temperature (Ambient Temperature)	-40	85	°C
C _{IN}	Input Capacitance		7	pF
t _{PU}	Power-up time for all VDDs to reach minimum specified voltage (power ramps must be monotonic)	0.05	500	ms

Table 6. Electrical Characteristics for CY2309AZI-XX Industrial Temperature Devices

Parameter	Description	Test Conditions	Min.	Max.	Unit
V _{IL}	Input LOW Voltage	CMOS Level, 30% of V _{DD}		0.25	V _{DD}
V _{IH}	Input HIGH Voltage	CMOS Level, 70% of V _{DD}	0.7		V _{DD}
I _{IL}	Input LOW Current	V _{IN} = 0V		50	μA
I _{IH}	Input HIGH Current	V _{IN} = V _{DD}		10	μA
I _{OL}	Output LOW Current ^[4] , (-1) (-1H)	V _{OL} = 0.5V	12		mA
			18		
I _{OH}	Output HIGH Current ^[4] , (-1) (-1H)	V _{OH} = V _{DD} - 0.5V		-12	mA
				-18	
I _{DDS}	Power-down Supply Current	REF = 0V S1 = V _{DD} , S2 = V _{DD}		50	μA
I _{DD}	Supply Current	Unloaded outputs @ 133 MHz		80	mA
		Loaded outputs @ 133 MHz, C _L = 10 pF		110	

Table 7. Switching Characteristics for CY2309AZI-1 Industrial Temperature Devices^[5]

Parameter	Name	Test Conditions	Min.	Typ.	Max.	Unit
	Reference Frequency		50		133	MHz
	Reference Edge Rate	30% to 70% of V _{DD}	0.5		4	V/ns
	Reference Duty Cycle		25		75	%
t ₁	Output Frequency	C _L = 15 pF	50		133	MHz
	Duty Cycle ^[4] = t ₂ / t ₁	Measured at VDD/2	40.0	50.0	60.0	%
t ₃	Rising Edge Rate ^[4] , (-1)	20% to 80% of V _{DD} , C _L = 15 pF	0.5		3	V/ns
	Rising Edge Rate ^[4] , (-1H)	20% to 80% of V _{DD} , C _L = 15 pF	0.8		4	V/ns
t ₄	Falling Edge Rate ^[4] , (-1)	80% to 20% of V _{DD} , C _L = 15 pF	0.5		3	V/ns
	Falling Edge Rate ^[4] , (-1H)	80% to 20% of V _{DD} , C _L = 15 pF	0.8		4	V/ns
TTB	Total Timing Budget window ^[6]	Outputs @ 133 MHz, Tracking Skew Not Included			650	ps

Note:

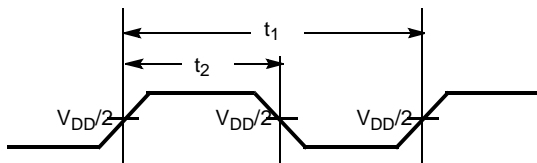
6. TTB is the window between the earliest and the latest output clocks with respect to the input reference clock across variations in output frequency, supply voltage, operating temperature, input clock edge rate, and process. The measurements are taken with the AC test load specified and include output-output skew, cycle-cycle jitter, and dynamic phase error. TTB will be equal to or smaller than the maximum specified value at a given output frequency.

Table 7. Switching Characteristics for CY2309AZI-1 Industrial Temperature Devices^[5]

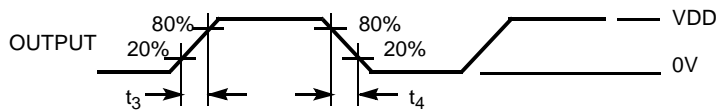
Parameter	Name	Test Conditions	Min.	Typ.	Max.	Unit
t_5	Output to Output Skew ^[4]	All Outputs Equally Loaded			200	ps
t_6	Input to Output Skew (Static Phase Error) ^[4]	Measured at $V_{DD}/2$, REF to CLKOUT			250	ps
t_7	Device to Device Skew ^[4]	Measured at $V_{DD}/2$			500	ps
t_J	Cycle to Cycle Jitter ^[4]	Loaded Outputs			200	ps
					35	psRMS
t_{LOCK}	PLL Lock Time ^[4]	Stable Power Supply, Valid Clock at REF			1.0	ms

Switching Waveforms

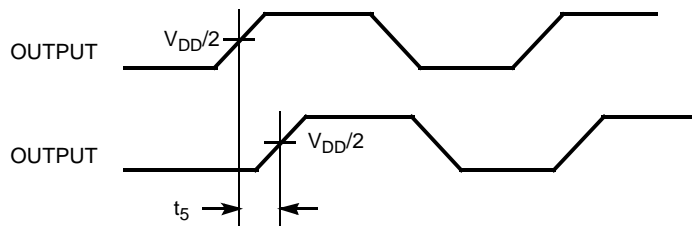
Duty Cycle Timing



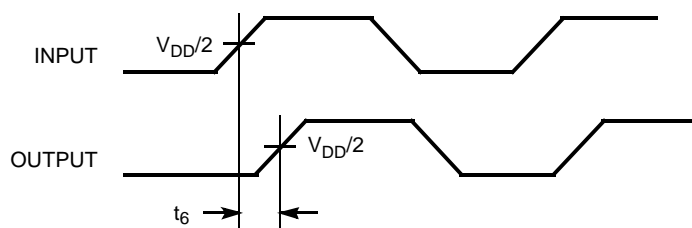
All Outputs Rise/Fall Time

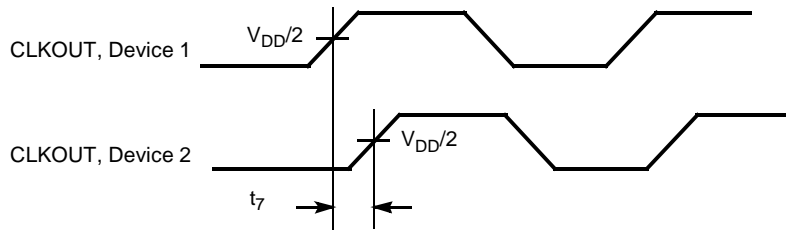
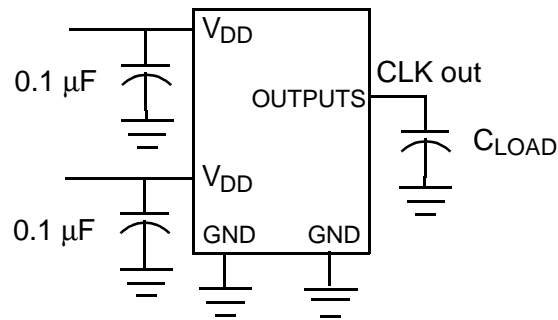


Output-Output Skew

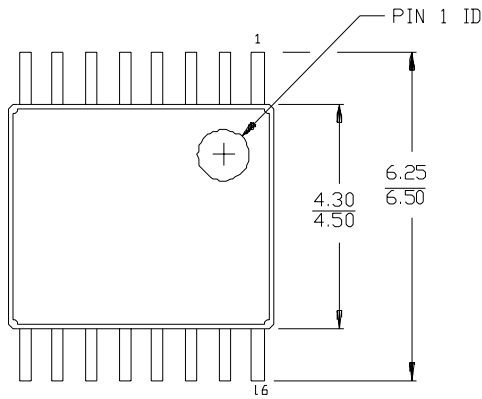


Input-Output Propagation Delay



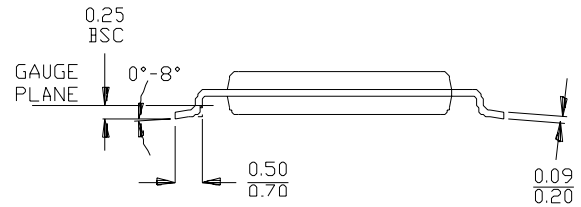
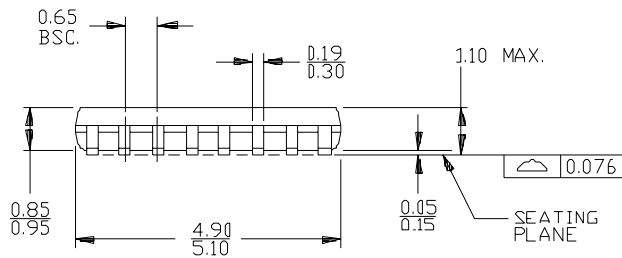
Switching Waveforms (continued)
Device-Device Skew

Test Circuits

Ordering Information

Ordering Code	Package Type	Operating Range
CY2309AZC-1	16-pin 4.4-mm TSSOP	Commercial, 0°C to 70°C
CY2309AZC-1T	16-pin 4.4-mm TSSOP – Tape and Reel	Commercial, 0°C to 70°C
CY2309AZC-1H	16-pin 4.4-mm TSSOP	Commercial, 0°C to 70°C
CY2309AZC-1HT	16-pin 4.4-mm TSSOP – Tape and Reel	Commercial, 0°C to 70°C
CY2309AZI-1	16-pin 4.4-mm TSSOP	Industrial, -40°C to 85°C
CY2309AZI-1T	16-pin 4.4-mm TSSOP – Tape and Reel	Industrial, -40°C to 85°C
CY2309AZI-1H	16-pin 4.4-mm TSSOP	Industrial, -40°C to 85°C
CY2309AZI-1HT	16-pin 4.4-mm TSSOP – Tape and Reel	Industrial, -40°C to 85°C

Package Drawing and Dimensions
16-pin Thin Shrunken Small Outline Package (4.40-MM Body) Z16


DIMENSIONS IN MILLIMETERS.

MIN.
MAX.



51-85091-**

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Document History Page

Document Title: CY2309A, Nine-Output, 200-MHz Zero Delay Buffer				
Document Number: 38-07378				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	115507	08/19/02	CTK	New Data Sheet
*A	121893	12/14/02	RBI	Power-up requirements added to Operating Conditions
*B	124598	03/06/03	RGL	Changed V_{IL} max. value in Commercial Temp. device from 0.3V to 0.25V Changed I_{DD} max. values in Commercial Temp. device from 75 and 150 to 115 and 145 mA, respectively Change V_{IL} max. value in Industrial Temp. device from 0.3V to 0.25V Changed I_{DD} max.values in Industrial Temp. device from 60 and 120 mA to 80 and 110 mA Removed Preliminary (final data sheet)